

**SWITCHING DIODES**
**FEATURES**

 Low forward voltage :  $V_F(3)=0.9V(\text{typ.})$ 

 Fast reverse recovery time :  $t_{rr}=1.6ns(\text{typ.})$ 
**MARKING: G3**
**MAXIMUM RATINGS** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse	$V_{RM}$	85	V
DC Blocking Voltage	$V_R$	80	V
Forward Continuous Current	$I_{FM}$	300	mA
Average Rectified Output	$I_O$	100	mA
Power Dissipation	$P_D$	150	mW
Junction temperature	$T_J$	125	$^\circ\text{C}$
Storage temperature range	$T_{STG}$	-55-125	$^\circ\text{C}$

**1SS196**

**ELECTRICAL CHARACTERISTICS** ( $T_{amb}=25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	$V_{(BR)R}$	80			V	$I_R=100\mu\text{A}$
Forward voltage	$V_{F1}$		0.60		V	$I_F=1\text{mA}$
	$V_{F2}$		0.72		V	$I_F=10\text{mA}$
	$V_{F3}$		0.90	1.2	V	$I_F=100\text{mA}$
Reverse current	$I_{R1}$			0.1	$\mu\text{A}$	$V_R=30\text{V}$
	$I_{R2}$			0.5	$\mu\text{A}$	$V_R=80\text{V}$
Capacitance between terminals	$C_T$		0.9	3.0	pF	$V_R=0, f=1\text{MHz}$
Reverse recovery time	$t_{rr}$		1.6	4.0	ns	$I_F=I_R=10\text{mA}, I_{rr}=0.1 \times I_R$

1SS196 Typical Characteristics

